

N-channel TrenchMOS standard level FET Rev. 02 — 8 July 2010

**Product data sheet** 

#### **Product profile** 1.

#### **1.1 General description**

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

#### 1.2 Features and benefits

- Higher operating power due to low thermal resistance
- Low conduction losses due to low on-state resistance

#### **1.3 Applications**

DC-to-DC convertors

#### **1.4 Quick reference data**

Suitable for high frequency applications due to fast switching characteristics

Switched-mode power supplies

Table 1.	Quick reference da	ta					
Symbol	Parameter	Conditions	M	in	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-		-	100	V
I <sub>D</sub>	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}$	-		-	47	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C	-		-	150	W
Static cha	aracteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C	-		22	25	mΩ
Dynamic	characteristics						
Q <sub>GD</sub>	gate-drain charge	$V_{GS}$ = 10 V; I <sub>D</sub> = 45 A; V <sub>DS</sub> = 80 V; T <sub>j</sub> = 25 °C	-		25	-	nC

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## 2. Pinning information

Table 2.	Pinning information				
Pin	Symbol	Description	Simplified outline	Graphic symbol	
1	G	gate	_	<u>_</u>	
2	D	drain <sup>[1]</sup>	mb		
3	S	source			
mb	D	mounting base; connected to drain		mbb076 S	
			SOT404 (D2PAK)		

[1] It is not possible to make connection to pin 2.

### 3. Ordering information

#### Table 3.Ordering information

Type number	Package		
	Name	Description	Version
PHB45NQ10T	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

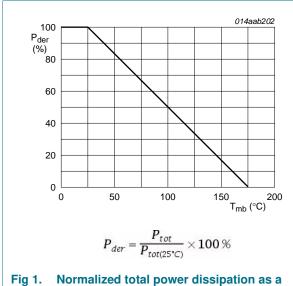
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### 4. Limiting values

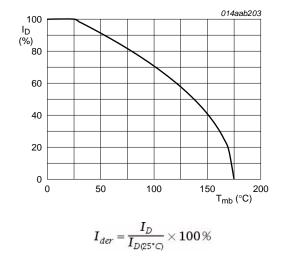
#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	100	V
V <sub>DGR</sub>	drain-gate voltage	T <sub>j</sub> ≤ 175 °C; T <sub>j</sub> ≥ 25 °C; R <sub>GS</sub> = 20 kΩ	-	100	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	$V_{GS} = 10 \text{ V}; \text{ T}_{mb} = 100 \text{ °C}$	-	33	А
		$V_{GS} = 10 \text{ V}; \text{ T}_{mb} = 25 \text{ °C}$	-	47	А
I <sub>DM</sub>	peak drain current	pulsed; T <sub>mb</sub> = 25 °C	-	188	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C	-	150	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drai	n diode				
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	-	47	А
I <sub>SM</sub>	peak source current	pulsed; T <sub>mb</sub> = 25 °C	-	188	А
Avalanche r	uggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$ \begin{array}{l} V_{GS} = 10 \text{ V};  T_{j(init)} = 25 \ ^{\circ}\text{C};  \text{I}_{\text{D}} = 40 \text{ A}; \\ V_{sup} \leq 25 \text{ V}; \text{ unclamped};  \text{t}_{p} = 100 \ \mu\text{s}; \\ R_{GS} = 50 \ \Omega \end{array} $	-	260	mJ
I <sub>AS</sub>	non-repetitive avalanche current	$V_{sup} \le 25 \text{ V}; V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C};$ $R_{GS} = 50 \Omega;$ unclamped	-	47	А



function of mounting base temperature





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# PHB45NQ10T

014aab216

10

t<sub>AV</sub> (ms)

25

1

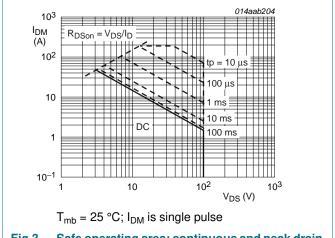
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T<sub>j</sub> prior to avalanche = 150 °C

10<sup>-1</sup>

Single-shot avalanche rating; avalanche

current as a function of avalanche period





### 5. Thermal characteristics

#### Table 5.Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base		-	-	1	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	mounted on printed-circuit board ; minimum footprint	-	50	-	K/W

10<sup>2</sup>

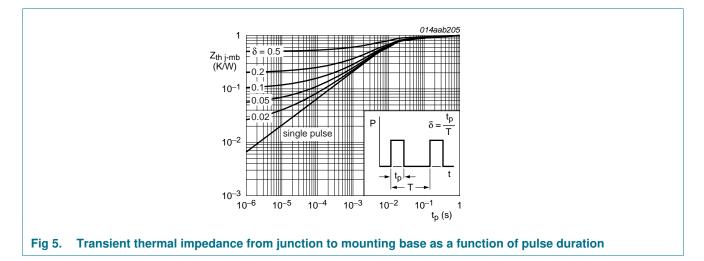
10

1 10<sup>-3</sup>

Fig 4.

10<sup>-2</sup>

I<sub>AS</sub> (A)



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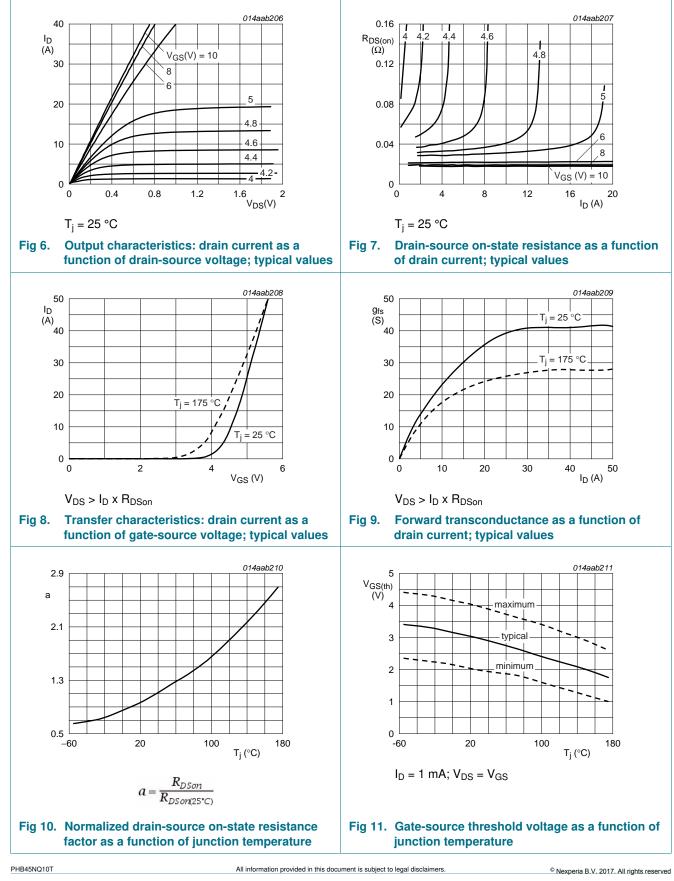
### 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static cha	aracteristics					
V <sub>(BR)DSS</sub> dr	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	89	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V
V <sub>GS(th)</sub>	gate-source threshold	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	6	V
	voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}$	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	2	3	4	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	100	nA
		$V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	100	nA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C	-	-	68	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C	-	22	25	mΩ
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 45 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 10 \text{ V};$	-	61	-	nC
Q <sub>GS</sub>	gate-source charge	$T_j = 25 \text{ °C}$	-	13	-	nC
Q <sub>GD</sub>	gate-drain charge		-	25	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	2600	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	340	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	195	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 50 \text{ V}; \text{ R}_{L} = 1.8 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	18	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5.6 \ \Omega; T_j = 25 \ ^{\circ}C$	-	72	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	69	-	ns
t <sub>f</sub>	fall time		-	58	-	ns
L <sub>D</sub>	internal drain inductance	from tab to centre of die ; $T_j = 25 \text{ °C}$	-	3.5	-	nH
L <sub>S</sub>	internal source inductance	from source lead to source bond pad ; $T_j = 25 ^\circ\text{C}$	-	7.5	-	nH
Source-d	rain diode					
V <sub>SD</sub>	source-drain voltage	$I_{S} = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_{j} = 25 \text{ °C}$	-	0.87	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S} = 20 \text{ A}; dI_{S}/dt = -100 \text{ A}/\mu s; V_{GS} = 0 \text{ V};$	-	82	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 25 V; T <sub>j</sub> = 25 °C	-	0.26	-	μC

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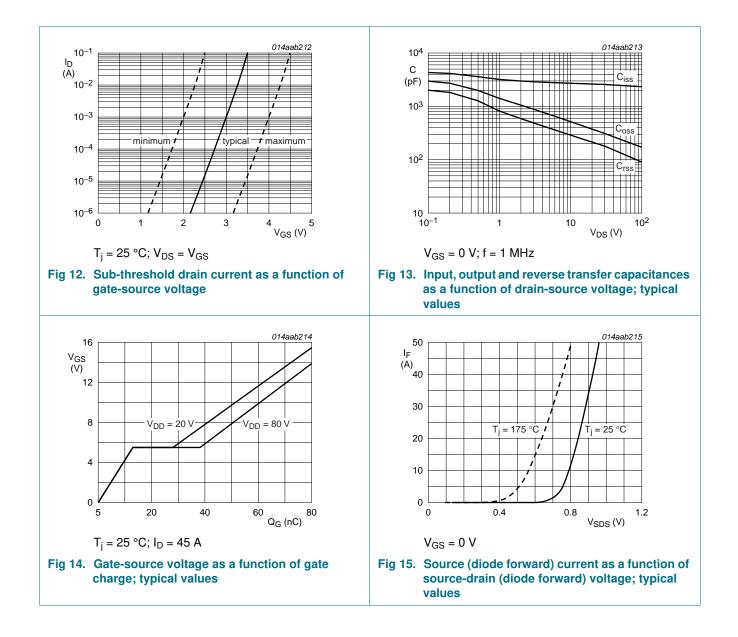
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### 7. Package outline

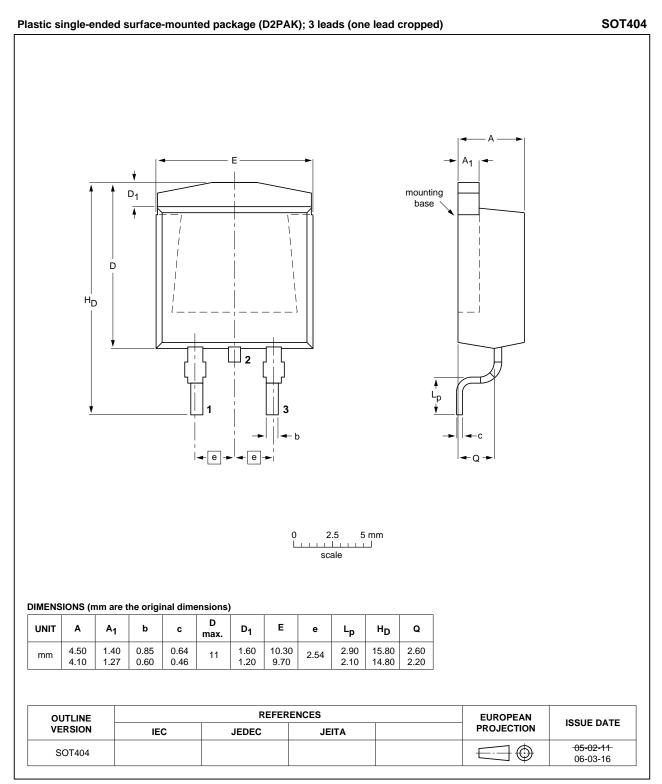


Fig 16. Package outline SOT404 (D2PAK)

PHB45NQ10T Product data sheet

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## 8. Revision history

Table 7.	<b>Revision history</b>						
Document ID		Release date	Data sheet status	Change notice	Supersedes		
PHB45NQ	10T v.2	20100708	Product data sheet	-	PHB_PHP_PHW45NQ10T v.1		
Modifications:		<ul> <li>The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li> </ul>					
		<ul> <li>Legal texts hat</li> </ul>	ve been adapted to the	new company na	ame where appropriate.		
		Type number	PHB45NQ10T separate	ed from data shee	t PHB_PHP_PHW45NQ10T v.1.		
PHB_PHP	_PHW45NQ10T v.1	19990801	Product specification	-	-		

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### 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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